

# **ISC Silicon NPN Power Transistor**

2SD312

## **DESCRIPTION**

- · High Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 600V(Min)
- · Fast Switching Speed
- · Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

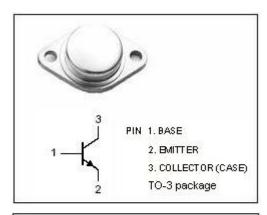


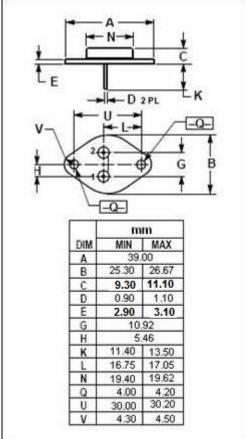
#### **APPLICATIONS**

- · Switching regulator and high voltage switching applications
- High speed DC-DC converter applications.

## ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	MAX	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	800	V	
Vceo	Collector-Emitter Voltage	600	٧	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
Ic	Collector Current-Continuous	0.5	А	
I <sub>CM</sub>	Collector Current-Peak	1	А	
Pc	Collector Power Dissipation @T <sub>C</sub> =100 °C	25	W	
Tj	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-65~150	${\mathbb C}$	







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 5mA; R <sub>BE</sub> = ∞	600			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	800			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	7			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.5A; I <sub>B</sub> = 0.1A			2.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 0.5A; I <sub>B</sub> = 0.1A			1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			100	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			10	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	10		40	
h <sub>FE-2</sub>	DC Current Gain	Ic= 0.5A; VcE= 5V	6			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 10V		5		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V		30		pF

### **NOTICE:**

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